In the Abstract:

ABSTRACT OF THE DISCLOSURE

~~Method for the production of a plurality of optoelectronic semiconductor chips and optoelectronic semiconductor chip~~

~~The invention relates to a~~ A method for the production of a plurality of optoelectronic semiconductor chips each having a plurality of structural elements with respectively at least one semiconductor layer. The method involves providing a chip composite base having a substrate and a growth surface. A non-closed mask material layer is grown onto the growth surface in such a way that the mask material layer has a plurality of statistically distributed windows having varying forms and/or opening areas, a mask material being chosen in such a way that a semiconductor material of the semiconductor layer that is to be grown in a later method step essentially cannot grow on said mask material or can grow in a substantially worse manner in comparison with the growth surface. Subsequently, semiconductor layers are deposited essentially simultaneously onto regions of the growth surface that lie within the windows. A further method step is singulation of the chip composite base with applied material to form semiconductor chips. ~~The invention additionally relates to an~~ An optoelectronic semiconductor component is produced according to the method.

~~Figure 1d~~